



## Specifications

### ◆ Maximum Ratings at $T_a=25$ , $T_c=25$ unless otherwise specified

Parameter	Symbol	Conditions	Ratings	UNIT
Operating substrate temperature	$T_C$ max	Recommended value is 105	115	
AC input voltage	$V_{AC}$	Specified test circuit	140	Vrms
Operating temperature	$T_{opr}$		-10 to+85	
Storage temperature	$T_{stg}$		-30 to+115	
Maximum output power	$W_o$ max	Specified test circuit $V_o=135V$	180	W

#### (TR1)

Drain current	$I_D$		10	A
Pulse drain current	$I_{D(Pulse)}$		35	A
Drain reverse current	$I_{DR}$		10	A
Gate-source voltage	$V_{GSS}$		$\pm 30$	V
Allowable power dissipation	$P_D$		100	W
Chip junction temperature	$T_j$ max		150	

#### (ZD1)

Allowable power dissipation	$P_{ZD1}$		500	mW
Chip junction temperature	$T_j(ZD1)max$		125	

### ◆ Recommended operating ranges at $T_a=25$

Parameter	Symbol	Conditions	Ratings	UNIT
Pin 4 input voltage	$V_4$		$\pm 8$ to $\pm 24$	V
Oscillator frequency	$f_{osc}$		20 to 100	kHz

### ◆ Operating characteristics at $T_a=25$ , $T_c=25$

( unless otherwise specified,specified test circuits)

Parameter	Symbol	Conditions	min	Typ	max	UNIT
<b>(TR1)</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	500			V
Gate-source cutoff voltage	$V_{GS(off)}$	$I_D=1mA, V_{DS}=10V$	2.5	3.5	5.0	V
ON resistance	$R_{DS(on)}$	$I_D=5A, V_{GS}=10V$		0.6	0.9	
Input capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		1400		pF
<b>(ZD1)</b>						
Zener voltage	$V_Z$	$I_Z=5mA$	23.7		26.3	V

### ◆ Series organization

These devices form a series with varying output power ratings

Type No.	Maximum ratings					Operating characteristics		
	V <sub>DSS</sub> [V]	T <sub>stg</sub> [ ]	T <sub>c</sub> max [ ]	T <sub>j</sub> max [ ]	I <sub>b</sub> [A]	Input voltage [V]	Output power [W]	ON resistance [ ]
STK73902	500	-30 to +115	+115	+150	6.0	85 to 132	110	1.4
STK73903					10.0		180	0.6
STK73904					12.0		210	0.55
STK73905					15.0		280	0.3
STK73906	900	-30 to +115	+115	+150	3.0	170 to 264	110	5.0
STK73907					5.0		180	3.0
STK73908					6.0		210	2.0
STK73909					8.0		280	1.2

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